B-8 Oral Session

Invited	Presentation No	Start	End	First name	FAMILY NAME	Affiliation	
24 Mon	Electrochem. &	& Bio: C	hair (T.N	lakamura, Al	(ST)		
Invited	B-8-I24-001	10:30	10:50	Michal	POMORSKI	CEA, LIST	Diamond for actinide traces detection an
	B-8-024-002	10:50	11:05	Yasuaki	EINAGA	Keio Univ.	Recent development on electroanalytical
	B-8-024-003	11:05	11:20	Stoffel	JANSSENS	Hasselt University	Phase Separation of Ethanol-Water Solu
	B-8-024-004	11:20	11:35	Amel	BENDALI	INSERM U968	Synthetic diamond and graphene based in
Invited	B-8-I24-005	11:35	11:50	Jin	ZHI	Technical Inst. of Physics and Chemistry, Chineses Academy of Scie	The fabrication of nanostructures of borc
Lunch		12:00	13:30				
	New plasma &	method	s.: Chair	(M.Pomorsk	i, CEA)		
	B-8-024-006	13:30	13:45	Takako	NAKAMURA	National Inst.of Advanced Industrial Science and Technol.	Sulfur-functionalized Diamond Powder
Invited	B-8-I24-007	13:45	14:05	Paul	MAY	University of Bristol	Microplasma arrays from CVD diamond
	B-8-024-008	14:05	14:20	Yonhua	TZENG	National Cheng Kung University	A new method of chemically enhanced d
	B-8-024-009	14:20	14:35	Kenji	NOSE	The Univ. Tokyo	High-resolution Raman spectroscopy for
	B-8-O24-010	14:35	14:50	Hamed	VAEZ-TAGHAVI	Tokyo Institute of Technology	Investigation of friction properties of Mg
Coffee break		15:00	15:15			•	
	NCD: Chair (K	.Haenen,	, Hasselt	U)			
Invited	B-8-I24-011	15:15	15:35	Oliver	WILLIAMS	Cardiff University	Nanocrystalline Diamond Films and Part
	B-8-O24-012	15:35	15:50	Cyril	POPOV	University of Kassel	AlN/Ultrananocrystalline Diamond High
	B-8-024-013	15:50	16:05	Sausan	AL-RIYAMI	Interdisciplinary Graduate School of Eng. Science, Kyushu Univ.	Nitrogen-Doped Ultrananocrystalline Di
	B-8-024-014	16:05	16:30	Xiaojun	HU	Zhejiang University of Technology	n-type doping of ultrananocrystalline dia
	NCD: Chair (O	.William	s, Cardif	fU)			
Invited	B-8-I24-015	16:30	16:50	Alexander	KROMKA	Institute of Physics of the ASCR, v.v.i.	Novel Perspectives of Nanocrystalline D
	B-8-024-016	16:50	17:05	Elisseos	VERVENIOTIS	Institute of Physics, ASCR, Czech Republic	Nanocrystalline Diamond Growth on a-S
	B-8-024-017	17:05	17:20	Emmanuel	SCORSONE	Research scientist	Resonant diamond MEMS biosensors fo
	B-8-O24-018	17:20	17:30	Ken	HAENEN	Hasselt University	Diamond nucleation on AlN and metals:
25 Tue	Detectors & S	ensor: C	hair (J.K	aneko. Hokk	aido U)		
Invited	B-8-I25-001	10:30	·	,	MORSE	European Synchrotron Radiation Facility	Single Crystal Diamond for Synchrotron
	B-8-025-002	10:50	11:05	Benoit	CAYLAR	CEA-LIST	Novel 3D micro-structuring of diamond
	B-8-O25-003	11:05	11:20	Meiyong	LIAO	National Institute for Materials Science	Strategies to develop single crystal diamo
Invited	B-8-I25-004	11:20	11:40	Jose	ALVAREZ	Laboratoire de Genie Electrique de Paris (LGEP)	Ultraviolet photodetectors based on hydr
	B-8-O25-005	11:40		Jie	SONG	State Key Laboratory of Superhard Materials	Various gas plasma etching processes of
T	D -0-025-005	12:00	13:30	510	50110	State reg Euroratory of Supernate Materials	various gas plasma eterning processes of
Lunch		12.00					
Lunch	Growth, donin	g eni: Cl		ezek ASCR			
	Growth, dopin	-	nair (B.R	. ,		University of Science and Technology Beijing	DC Arc Plasma let Growth of Large Are
Invited	B-8-I25-006	13:30	nair (B.R 13:50	Fanxiu	LU	University of Science and Technology Beijing	-
	B-8-I25-006 B-8-I25-007	13:30 13:50	nair (B.R 13:50 14:10	Fanxiu Richard	LU BALMER	Element Six	Synthesis and Characterisation of Boron
Invited	B-8-I25-006 B-8-I25-007 B-8-O25-008	13:30 13:50 14:10	nair (B.R 13:50 14:10 14:25	Fanxiu Richard Yuki	LU BALMER YOKOYAMA	Element Six Waseda University	Synthesis and Characterisation of Boron Electric property of diamond surface cov
Invited Invited	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009	13:30 13:50 14:10 14:25	nair (B.R 13:50 14:10 14:25 14:40	Fanxiu Richard	LU BALMER	Element Six	Synthesis and Characterisation of Boron Electric property of diamond surface cov
Invited	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009	13:30 13:50 14:10 14:25 15:00	nair (B.R 13:50 14:10 14:25 14:40 15:15	Fanxiu Richard Yuki Akira	LU BALMER YOKOYAMA	Element Six Waseda University	Synthesis and Characterisation of Boron Electric property of diamond surface cov
Invited Invited Coffee break	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 C Device: Chair	13:30 13:50 14:10 14:25 15:00 (S.Koizu	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS	Fanxiu Richard Yuki Akira	LU BALMER YOKOYAMA DAICHO	Element Six Waseda University Waseda University	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for pa
Invited Invited	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35	Fanxiu Richard Yuki Akira S) Tsuyoshi	LU BALMER YOKOYAMA DAICHO FUNAKI	Element Six Waseda University Waseda University Osaka University	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for pa Power Switching Characteristics of a Dia
Invited Invited Coffee break	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010 B-8-O25-011	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15 15:35	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35 15:50	Fanxiu Richard Yuki Akira S) Tsuyoshi Arie	LU BALMER YOKOYAMA DAICHO FUNAKI NAWAWI	Element Six Waseda University Waseda University Osaka University Nanyang Technological University	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for pa Power Switching Characteristics of a Dia Device fabrication and modeling of high
Invited Invited Coffee break	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010 B-8-O25-011 B-8-O25-012	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15 15:35 15:35	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35 15:50 16:05	Fanxiu Richard Yuki Akira S) Tsuyoshi Arie Tomoya	LU BALMER YOKOYAMA DAICHO FUNAKI NAWAWI NARUO	Element Six Waseda University Waseda University Osaka University Nanyang Technological University Waseda University	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for pa Power Switching Characteristics of a Dia Device fabrication and modeling of high Diamond MOSFET with O-terminated t
Invited Invited Coffee break	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010 B-8-O25-011 B-8-O25-012 B-8-O25-013	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15 15:35 15:50 16:05	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35 15:50 16:05 16:25	Fanxiu Richard Yuki Akira S) Tsuyoshi Arie Tomoya Bohuslav	LU BALMER YOKOYAMA DAICHO FUNAKI NAWAWI	Element Six Waseda University Waseda University Osaka University Nanyang Technological University	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for pa Power Switching Characteristics of a Dia Device fabrication and modeling of high Diamond MOSFET with O-terminated t
Invited Invited Coffee break Invited	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010 B-8-O25-011 B-8-O25-012 B-8-O25-013 Device: Chair	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15 15:35 15:50 16:05 (H.Umez	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35 15:50 16:05 16:25 :awa, Als	Fanxiu Richard Yuki Akira Tsuyoshi Arie Tomoya Bohuslav	LU BALMER YOKOYAMA DAICHO FUNAKI NAWAWI NARUO REZEK	Element Six Waseda University Waseda University Osaka University Nanyang Technological University Waseda University Institute of Physics ASCR, v. v. i.	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for pa Power Switching Characteristics of a Dia Device fabrication and modeling of high Diamond MOSFET with O-terminated t Spatially-resolved photovoltage in B-dop
Invited Invited Coffee break	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010 B-8-O25-011 B-8-O25-012 B-8-O25-013 Device: Chair B-8-I25-014	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15 15:35 15:50 16:05 (H.Umez 16:30	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35 15:50 16:05 16:25 cawa, AIS 16:50	Fanxiu Richard Yuki Akira Akira 5) Tsuyoshi Arie Tomoya Bohuslav 57) Tokuyuki	LU BALMER YOKOYAMA DAICHO FUNAKI NAWAWI NARUO REZEK TERAJI	Element Six Waseda University Waseda University Osaka University Nanyang Technological University Waseda University Institute of Physics ASCR, v. v. i. National Institute for Materials Science	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for pa Power Switching Characteristics of a Dia Device fabrication and modeling of high Diamond MOSFET with O-terminated t Spatially-resolved photovoltage in B-dop p-type diamond Schottky diodes -current
Invited Invited Coffee break Invited	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010 B-8-O25-011 B-8-O25-012 B-8-O25-013 Device: Chair B-8-I25-014 B-8-I25-014	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15 15:35 15:50 16:05 (H.Umez 16:30 16:50	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35 15:50 16:05 16:05 16:25 :awa, Als 16:50 17:05	Fanxiu Richard Yuki Akira Tsuyoshi Arie Tomoya Bohuslav ST) Tokuyuki Shaoheng	LU BALMER YOKOYAMA DAICHO FUNAKI NAWAWI NARUO REZEK TERAJI CHENG	Element Six Waseda University Waseda University Osaka University Nanyang Technological University Waseda University Institute of Physics ASCR, v. v. i. National Institute for Materials Science 1-1 Namiki, Tsukuba, Ibaraki 305-0044, Japan	Synthesis and Characterisation of Boron Electric property of diamond surface cov Atomic layer deposition of Al2O3 for par Power Switching Characteristics of a Dia Device fabrication and modeling of high Diamond MOSFET with O-terminated th Spatially-resolved photovoltage in B-dop p-type diamond Schottky diodes -current High dielectric constant oxide on diamor
Invited Invited Coffee break Invited	B-8-I25-006 B-8-I25-007 B-8-O25-008 B-8-O25-009 Device: Chair B-8-I25-010 B-8-O25-011 B-8-O25-012 B-8-O25-013 Device: Chair B-8-I25-014	13:30 13:50 14:10 14:25 15:00 (S.Koizu 15:15 15:35 15:50 16:05 (H.Umez 16:30	nair (B.R 13:50 14:10 14:25 14:40 15:15 mi,NIMS 15:35 15:50 16:05 16:25 cawa, AIS 16:50	Fanxiu Richard Yuki Akira Akira 5) Tsuyoshi Arie Tomoya Bohuslav 57) Tokuyuki	LU BALMER YOKOYAMA DAICHO FUNAKI NAWAWI NARUO REZEK TERAJI	Element Six Waseda University Waseda University Osaka University Nanyang Technological University Waseda University Institute of Physics ASCR, v. v. i. National Institute for Materials Science	DC Arc Plasma Jet Growth of Large Area Synthesis and Characterisation of Boron Electric property of diamond surface cove Atomic layer deposition of Al2O3 for par Power Switching Characteristics of a Dia Device fabrication and modeling of high Diamond MOSFET with O-terminated th Spatially-resolved photovoltage in B-dop p-type diamond Schottky diodes -current High dielectric constant oxide on diamon Electrical property of high-k insulator/p-o Diamond electronic devices

Poster Session

Pr	esentation No	Start	End	First name	FAMILY NAME	Affiliation	Abstract title
Gro	owth						
B-8	S-P24-001	18:00	20:00	Yoshiaki	MOKUNO	National Institute of Advanced Industrial Science and Technology	Observation of Ion Implantation Lift-off Surface of Single Crystal Diamond
B-8	3-P24-002	18:00	20:00	Hong-Xing	WANG	Diamond CVD systems department	Application of microwave plasma chemical vapor deposition system to single crystal diamond growth
B-8	3-P24-003	18:00	20:00	Ryota	SATAKE	Hokkaido University	Growth and evaluation of hexagonal boron nitride using metal solvent in radio-frequency heating furnace
B-8-P24-004 18:00 20:00 Hitoshi SUMIYA S		Sumitomo Electric Industries, Ltd.	HPHT synthesis of defect free large type-IIa diamond				
B-8	3-P24-005	18:00	20:00	Vitaly	BORMASHOV	Technological Institute for Superhard and Novel Carbon Materials	High Quality Low-doped Semiconductor Synthetic Single-Crystal Diamonds
SAV	SAW&MEMS						
B-8	S-P24-006	18:00	20:00	Satoshi	FUJII	Chiba University	Study on a one-port SAW resonator using a single crystal diamond
B-8	S-P24-007	18:00	20:00	Emmanuel	SCORSONE	Research scientist	Diamond Micro Electrode Array (MEA) as electrophysiology platforms with high performance and stability
NC	D & films						
B-8	3-P24-008	18:00	20:00	Shinya	OHMAGARI	Kyushu University	Photodetection properties of ultrananocrystalline diamond/hydrogenated amorphous carbon composite films
B-8	3-P24-009	18:00	20:00	Shinichi	SHIKATA	AIST	Thermal conductivity of nano-crystalline diamon
B-8	3-P24-010	18:00	20:00	Sausan	AL-RIYAMI	Interdisciplinary Graduate School of Engineering Science, Kyushu	Hetrojunction Diodes Comprised of p-Type Si/n-Type UNCD:a-CH Composite Film Prepared by Pulsed Laser Deposition.
B-8	3-P24-011	18:00	20:00	Yonhua	TZENG	National Cheng Kung University	UNCD encapsulated NDD micro-heater for chemical and bio-compatible applications
B-8	S-P24-012	18:00	20:00	Jaeho	KIM	National Institute of Advanced Industrial Science and Technology	Atmospheric pressure synthesis of nanocrystalline diamond films by a microwave plasma jet
B-8	S-P24-013	18:00	20:00	Mai	TAKASHIMA	Tokyo Institute of Technology	Hydrogen content and mechanical characteristics of DLC films
QE	& Isotope						
	3-P24-014	18:00	20:00	Cyril	POPOV	University of Kassel	Investigation of NV Centers in Diamond Nanopillars
B-8	3-P24-015	18:00	20:00	Kohei	OHASHI	Keio University	Nitrogen-Vacancy Centers Introduced during CVD Growth in Isotopically Controlled 12C Diamond Films
B-8	3-P24-016	18:00	20:00	Syuhei	TOMIZAWA	Keio University	Effective and Position-controlled Doping of Nitrogen-Vacancy Centers Using Cheminal Vapor Deposition on Etched Substrate
B-8	S-P24-017	18:00	20:00	Hideyuki	WATANABE	National Institute of Advanced Industrial Science and Technology (A	Raman scattering from optical phonons in isotopic 12C13C diamond superlattices
B-8	3-P24-018	18:00	20:00	tokuyuki	TERAJI	National Institute for Materials Science	Isotopically-enriched 12C diamond films
B-8	S-P24-019	18:00	20:00	Kazuhiro	IKEDA	Sumitomo Electric Industries	Isotope enrichment of high-purity HPHT diamond
Def	fects						
B-8	3-P24-020	18:00	20:00	Yasuji	MURAMATSU	University of Hyogo	Detection of Defects/Dangling-Bonds in Diamond by the Synchrotron Radiation Excited X-Ray Emission Spectroscopy
B-8	S-P24-021	18:00	20:00	Yukako	КАТО	National Institute of Advanced Industrial Science and Technology	Effect of substrate pre-treatment for the single-crystal CVD diamond growth
B-8	3-P24-023	18:00	20:00	Wataru	KADA	Japan Atomic Energy Agency	Transient Ion-Beam-Induced Current (TIBIC) Analysis of the Irradiation Effects in Transmission CVD Diamond Film Detectors
Dev	vices						
B-8	3-P24-024	18:00	20:00	Hitoshi	UMEZAWA	National Institute of Advanced Industrial Science and Technology	High current operation of diamond vertical-SBDs at 250oC
B-8	3-P24-025	18:00	20:00	Nobuteru	TSUBOUCHI	National Institute of Advanced Industrial Science and Technology (A	Structural and electrical properties of diamond with high-dose ion implantation at elevated temperatures: dependence of ion species
B-8	3-P24-026	18:00	20:00	Kiran Kuma	KOVI	Uppsala University	Surface Passivation of SC-CVD Diamond by High-k Dielectrics.
B-8	3-P24-027	18:00	20:00	Masataka	IMURA	National Institute for Materials Science (NIMS)	Al2O3/Diamond Field Effect Transistors using Surface p-Channel Prepared by Thermal Treatment with Hydrogen and Ammonia A
-	S-P24-028	18:00	20:00	Etienne	GHEERAERT	Universite Joseph Fourier	Hole and electronic conductivity in compensated n- and p-type doped diamond
	S-P24-029	18:00		Satoshi	KOIZUMI	National Institute for Materials Science (NIMS)	SIMS analysis of delta-doped diamond structures
-	S-P24-030	18:00				Division for Electricity, Uppsala University	Low Temperature Hole Transport in Single Crystal Synthetic Diamond

Abstract title
d spectrometry in liquids
application of boron-doped diamond electrodes
tions at Diverse Terminated Diamond Surfaces
mplants for neuroprostheses applications: from biocompatibility to interaction with tissues
n-doped diamond electrodes
Surface for Attachment of Gold and Biomolecules
Surface for Attachment of Gold and Bromolecules
liamond nucleation by microwave plasma CVD
diamond-like carbon thin film
g-doped amorphous carbon films deposited in electron beam excited plasma
2 - F
ticles
Frequency SAW Nano Device
amond/Hydrogen-Free Amorphous Carbon Composite Films Prepared by Pulsed Laser Deposition
mond films by ion implantation
biamond Films
ii:H
or trace detection in liquids
Influence of plasma pretreatments
X-ray Beam Monitoring
for radiation detector applications: enhanced performances evaluated under particles and photons beams.
ond deep-ultraviolet detectors
rogenated/oxidized diamond surfaces
diamonds coated with a gold layer
a High Quality Exceptonding Diamond Films and Applications to the Industry in Chine
a High Quality Freestanding Diamond Films and Applications to the Industry in China
Delta-Doped Diamond Devices for ered with AlN grown by MBE
ssivating hydrogen-terminated diamond
amond Schottky Barrier Diode
temperature, high power diamond vertical Schottky barrier diode
hin boron doped channel
bed diamond Schottky diode
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transport mechanisms and
nd for high power devices
diamond diodes for electric field controlling